

SEB160V-40
Schottky barrier diode

Revision:A

Features

- Small power mold type. (PMDS)
- Low I_R
- High reliability

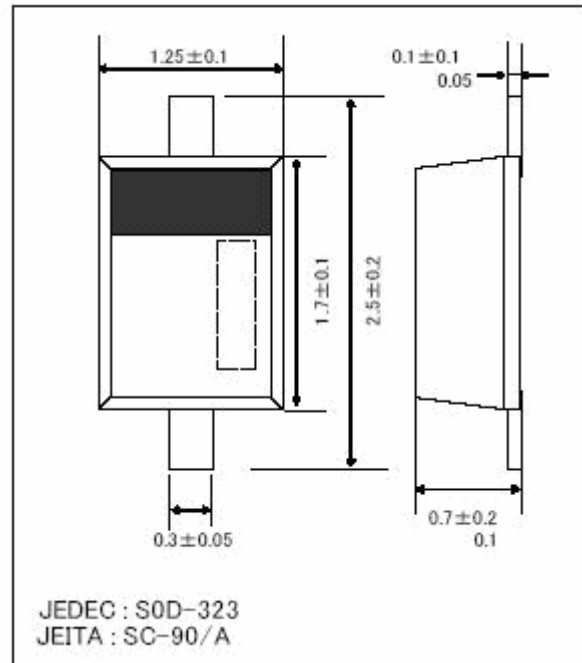
Applications

- General rectification

Construction

- Silicon epitaxial planer

● **External dimensions (Unit : mm)**



Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	I_O	1	A
Forward current surge peak	T_{FSM}	30	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 ~ +150	°C

(*1) Mounted on epoxy board. 180° Half sine wave

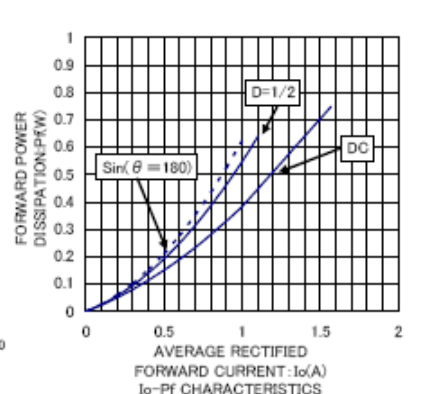
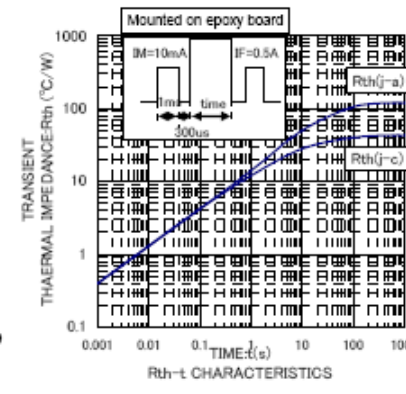
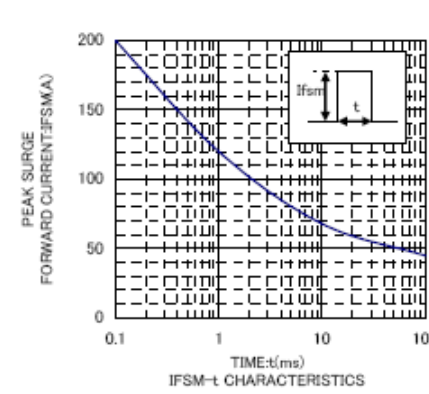
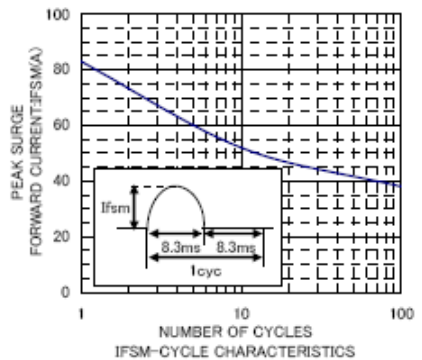
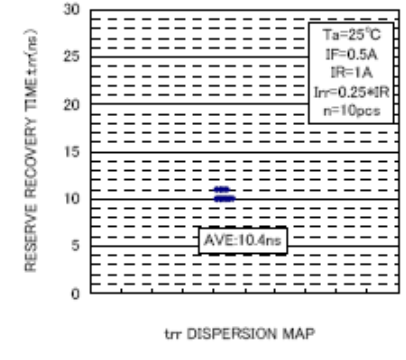
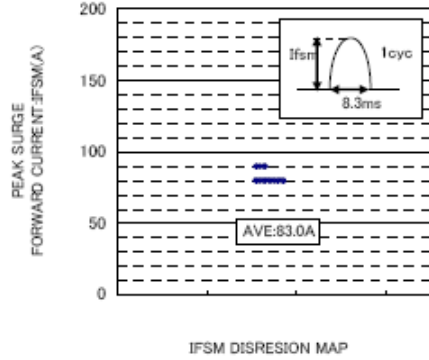
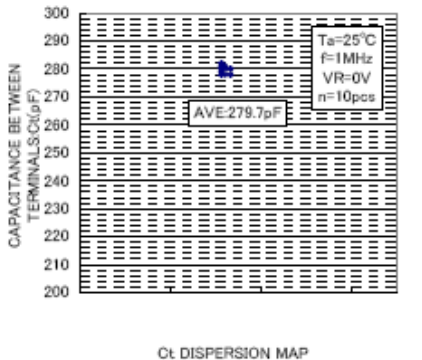
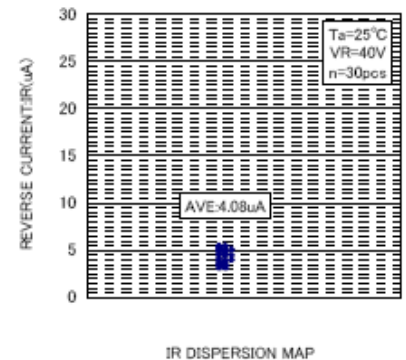
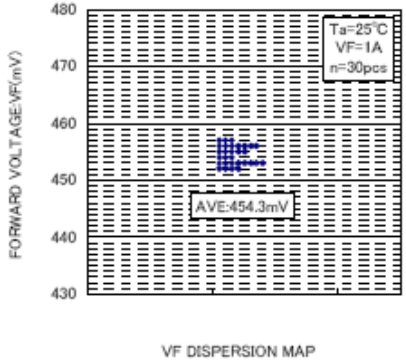
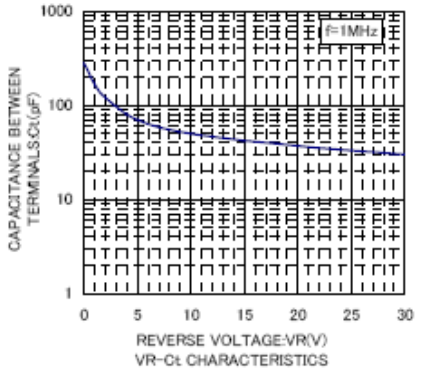
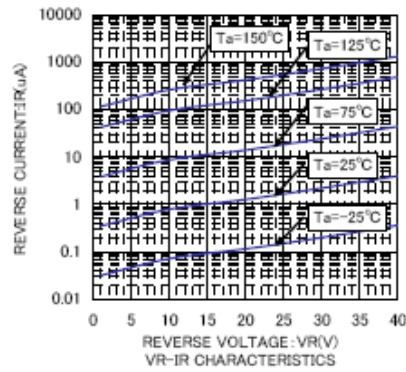
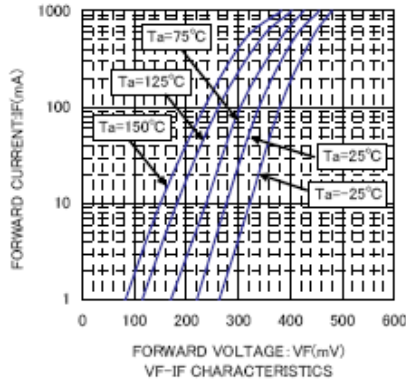
Electrical characteristics (Ta=25°C)

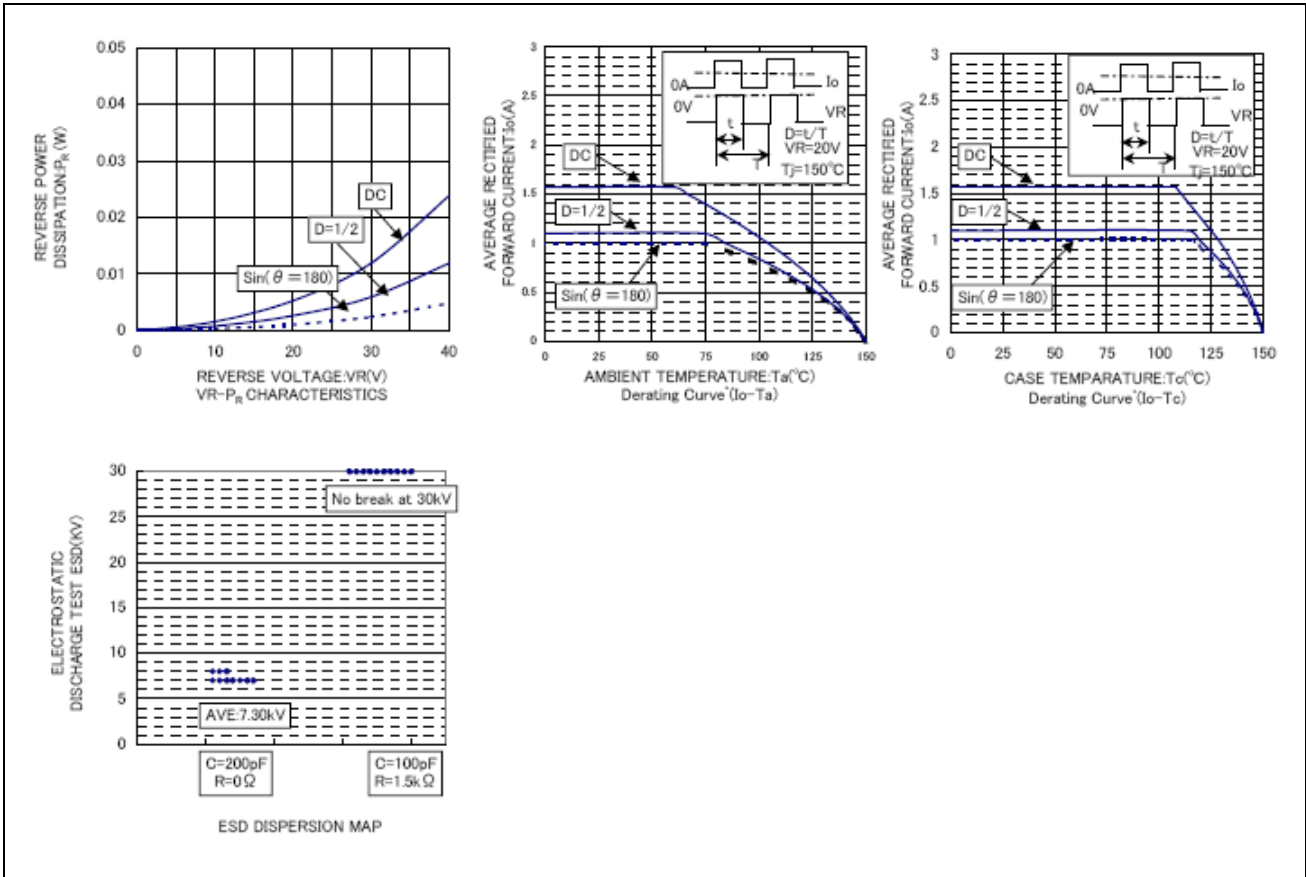
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.46	0.51	V	$I_F = 1.0A$
Reverse current	I_R	—	4.0	30	uA	$V_R = 40V$

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- Please pay attention to static electricity when handling.

●Electrical characteristic curves (Ta=25°C)





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